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U.S.S.N. 10/055,134

**Listing of the Claims**

1. - 27. (Cancelled)

28. (Original) A semiconductor structure of a damascene or dual damascene interconnect formed by a trench-filling process of electroplated Cu having an as-deposited grain size of not less than 0.5  $\mu\text{m}$  and a decrease in electrical resistance of at least 15% after a time period of not more than 30 hours at about 21°C.

29. (Currently amended) A semiconductor structure of a damascene or dual damascene interconnect according to claim 28, wherein said as-deposited grain size of electroplated Cu is between about 0.5  $\mu\text{m}$  and about [[.15]] 1.5  $\mu\text{m}$ .

30. (Original) A semiconductor structure of a damascene or dual damascene interconnect according to claim 28, wherein said grain size of said electroplated Cu after said time period of not more than 30 hours at about 21°C is between about 1.5  $\mu\text{m}$  and about 2  $\mu\text{m}$ .